

2SK1868

Silicon N-Channel Power F-MOS

■ Features

- Avalanche energy capability guaranteed : $E_{AS} > 62.5\text{mJ}$
- Low ON-resistance $R_{DS(on)}$: $R_{DS(on)1} = 0.135\Omega$
- High-speed switching : $t_f = 53\text{ns}$
- No secondary breakdown
- Low-voltage drive possible ($V_{GS} = 4\text{V}$)
- Radial taping possible

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

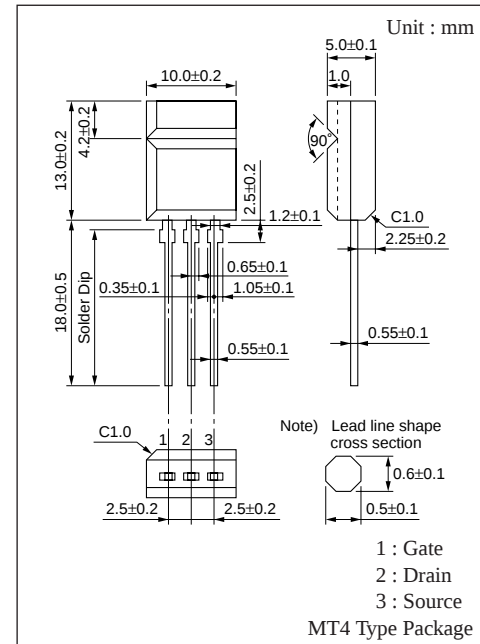
■ Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$)

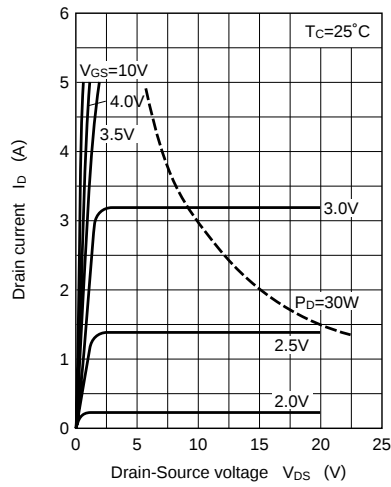
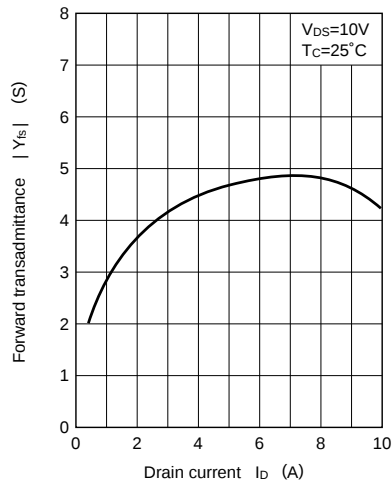
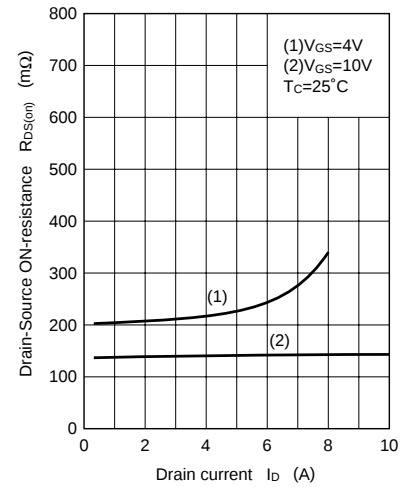
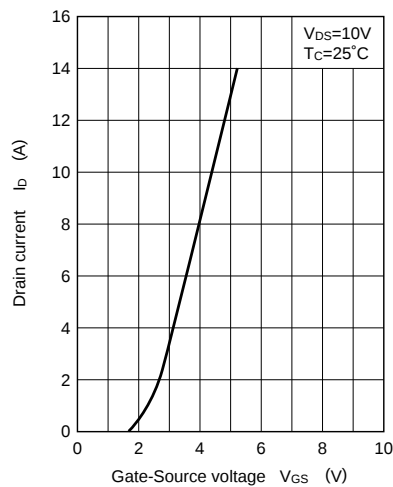
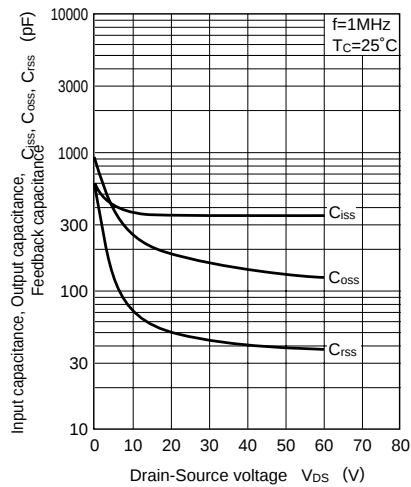
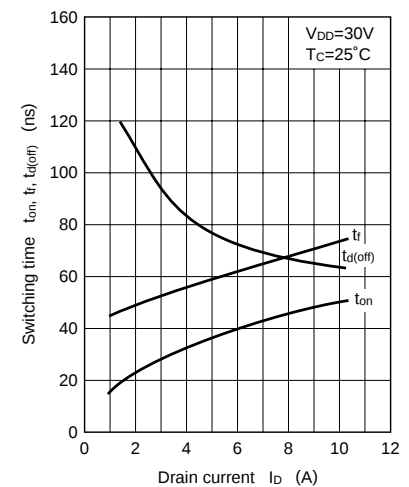
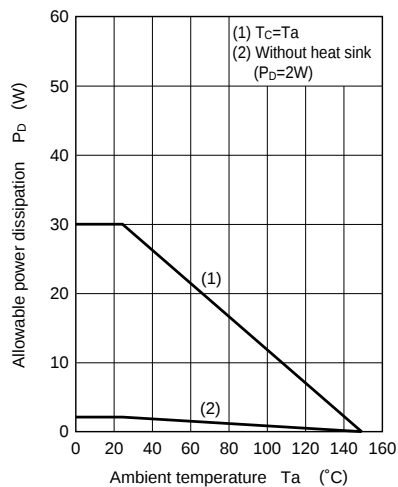
Parameter	Symbol	Rating	Unit
Drain-Source breakdown voltage	V_{DSS}	60	V
Gate-Source voltage	V_{GSS}	± 20	V
Drain current	DC	I_D^*	A
		I_D	A
	Pulse	I_{DP}	A
Avalanche energy capability	E_{AS}^{*2}	62.5	mJ
Allowable power dissipation	$T_c = 25^\circ\text{C}$	P_D	15
	$T_a = 25^\circ\text{C}$	P_D	2
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* 1 Max I_D value at 4V drive * 2 $L = 5\text{mH}$, $I_L = 5\text{A}$, $V_{DD} = 10\text{V}$, 1 pulse

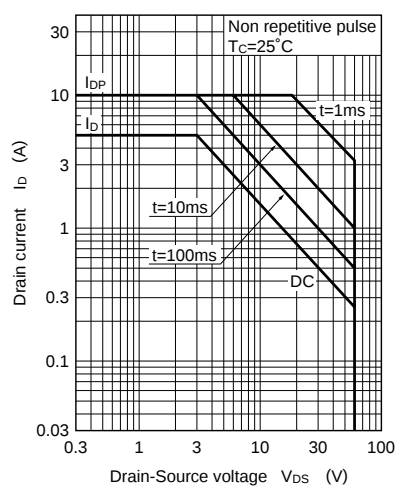
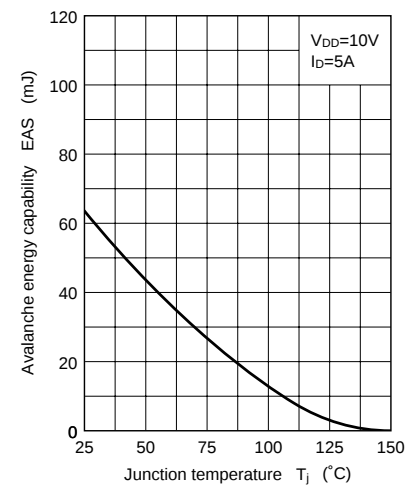
■ Electrical Characteristics ($T_c = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I_{DSS}	$V_{DS} = 60\text{V}$, $V_{GS} = 0$			0.1	μA
Gate-Source leakage current	I_{GSS}	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0$			± 1	μA
Drain-Source breakdown voltage	V_{DSS}	$I_D = 1\text{mA}$, $V_{GS} = 0$	60			V
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{V}$, $I_D = 1\text{mA}$	1		2.5	V
Drain-Source ON-resistance	$R_{DS(on)1}$	$V_{GS} = 10\text{V}$, $I_D = 3\text{A}$		135	200	$\text{m}\Omega$
	$R_{DS(on)2}$	$V_{GS} = 4\text{V}$, $I_D = 2\text{A}$		200	300	$\text{m}\Omega$
Forward transadmittance	$ Y_{fs} $	$V_{DS} = 10\text{V}$, $I_D = 3\text{A}$	2.4	4		S
Diode forward voltage	V_{DSF}	$I_{DR} = 5\text{A}$, $V_{GS} = 0$			-1.7	V
Input capacitance	C_{iss}	$V_{DS} = 10\text{V}$, $V_{GS} = 0$, $f = 1\text{MHz}$		400		pF
Output capacitance	C_{oss}			210		pF
Feedback capacitance	C_{rss}			80		pF
Turn-on time	t_{on}	$V_{GS} = 10\text{V}$, $I_D = 3\text{A}$ $V_{DD} = 30\text{V}$, $R_L = 10\Omega$		29		ns
Fall time	t_f			53		ns
Turn-off time (delay time)	$t_{d(off)}$			97		ns
Channel-Case heat resistance	$R_{th(ch-c)}$				8.33	$^\circ\text{C/W}$

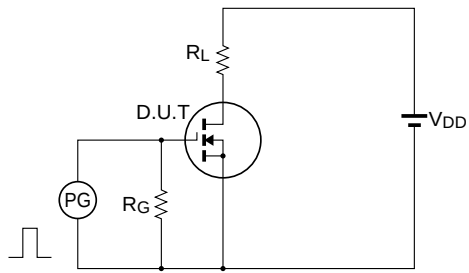


$I_D - V_{DS}$  $|Y_{fs}| - I_D$  $R_{DS(on)} - I_D$  $I_D - V_{GS}$  $C_{iss}, C_{oss}, C_{rss} - V_{DS}$  $t_{on}, t_f, t_d(off) - I_D$  $P_D - T_a$ 

Area of safe operation (ASO)

 $EAS - T_j$ 

Switching measurement circuit



Avalanche capability test circuit

